Growth of Ordered Graphene Ribbons by Sublimation Epitaxy

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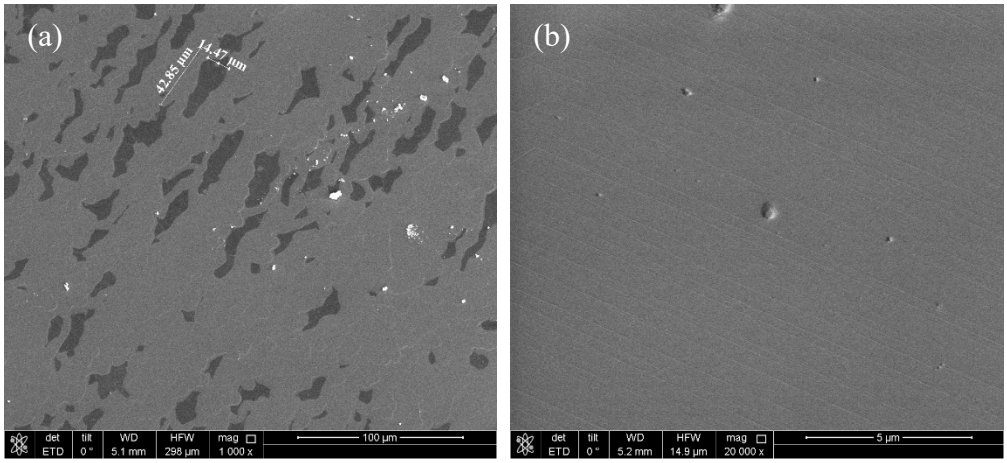
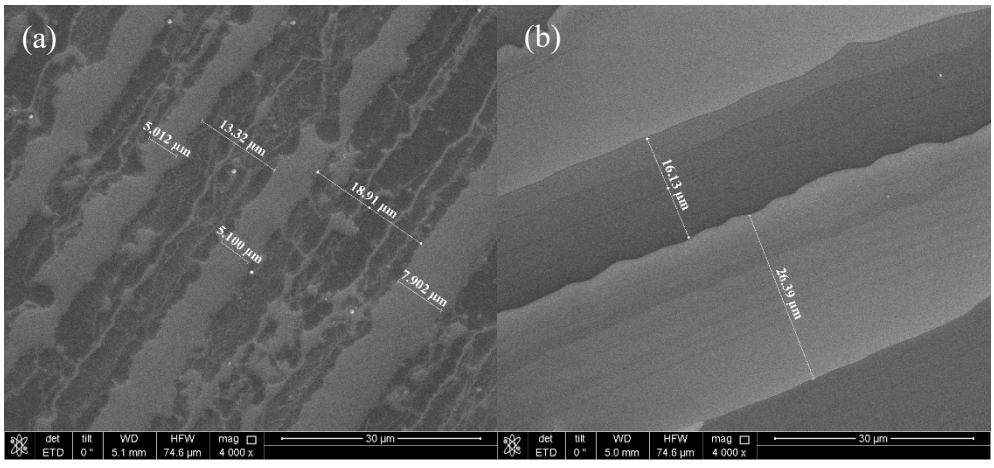


Figure S1. Scanning electron microscope (SEM) images of (**a**) surface of Wafer A; (**b**) surface of target wafer after a heat treatment.



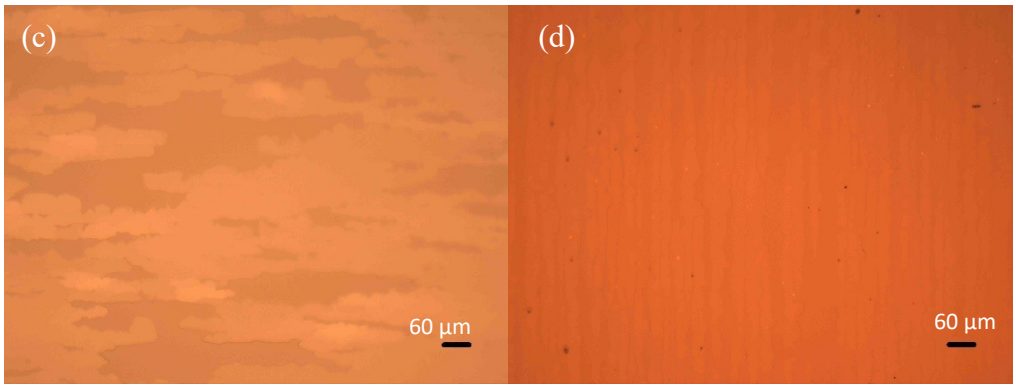


Figure S2. SEM images of surface of (**a**) Wafer C1 and (**b**) Wafer C2; optical images of surface of (**c**,**d**) Wafer C2.

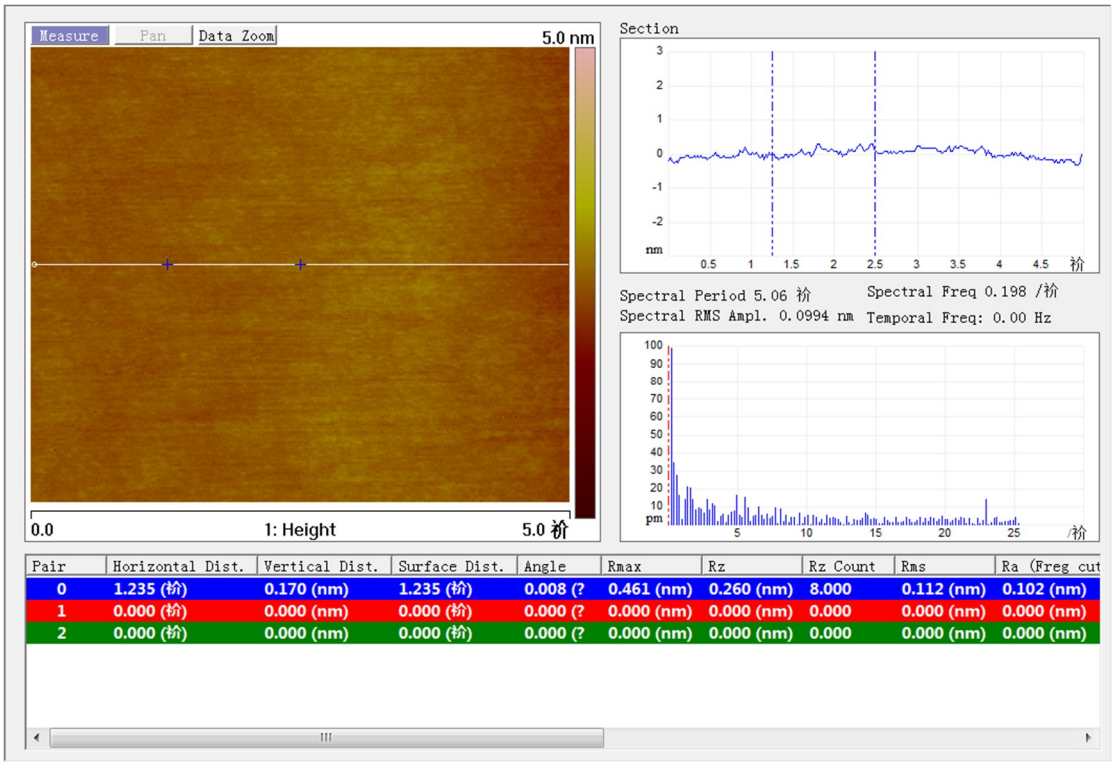


Figure S3. A 5 µm × 5 µm atomic force microscopy (AFM) analysis of dark ribbon on the surface of Wafer C2.

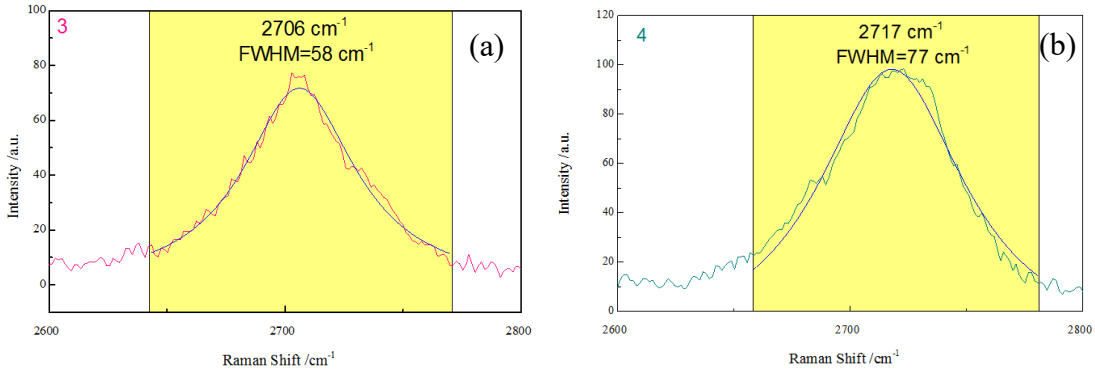


Figure S4. Lorentz fitting and the FWHM of 2D peak of Raman spectrum of (**a**) point 3 and (**b**) point 4.